

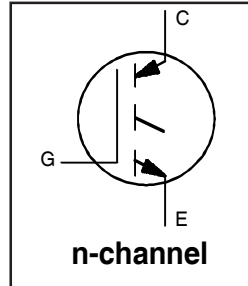
# IRG4PH50SPbF

INSULATED GATE BIPOLAR TRANSISTOR

Standard Speed IGBT

## Features

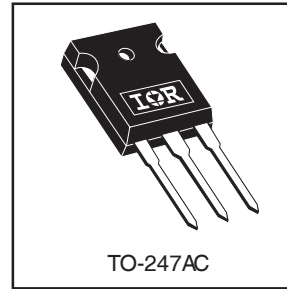
- Standard: Optimized for minimum saturation voltage and low operating frequencies ( < 1kHz)
- Generation 4 IGBT design provides tighter parameter distribution and higher efficiency than Generation 3
- Industry standard TO-247AC package
- Lead-Free



$V_{CES} = 1200V$
$V_{CE(on) typ.} = 1.47V$
@ $V_{GE} = 15V, I_C = 33A$

## Benefits

- Generation 4 IGBT's offer highest efficiency available
- IGBT's optimized for specified application conditions
- Designed to be a "drop-in" replacement for equivalent industry-standard Generation 3 IR IGBT's



## Absolute Maximum Ratings

	Parameter	Max.	Units
$V_{CES}$	Collector-to-Emitter Voltage	1200	V
$I_C @ T_C = 25^\circ C$	Continuous Collector Current	57	A
$I_C @ T_C = 100^\circ C$	Continuous Collector Current	33	
$I_{CM}$	Pulsed Collector Current <sup>①</sup>	114	
$I_{LM}$	Clamped Inductive Load Current <sup>②</sup>	114	
$V_{GE}$	Gate-to-Emitter Voltage	$\pm 20$	V
$E_{ARV}$	Reverse Voltage Avalanche Energy <sup>③</sup>	270	mJ
$P_D @ T_C = 25^\circ C$	Maximum Power Dissipation	200	W
$P_D @ T_C = 100^\circ C$	Maximum Power Dissipation	80	
$T_J$	Operating Junction and	-55 to +150	°C
$T_{STG}$	Storage Temperature Range		
	Soldering Temperature, for 10 sec.	300 (0.063 in. (1.6mm) from case)	
	Mounting torque, 6-32 or M3 screw.	10 lbf•in (1.1N•m)	

## Thermal Resistance

	Parameter	Typ.	Max.	Units
$R_{\theta JC}$	Junction-to-Case	---	0.64	°C/W
$R_{\theta CS}$	Case-to-Sink, Flat, Greased Surface	0.24	---	
$R_{\theta JA}$	Junction-to-Ambient, typical socket mount	---	40	
Wt	Weight	6.0 (0.21)	---	g (oz)

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## Electrical Characteristics @ $T_J = 25^\circ\text{C}$ (unless otherwise specified)

	Parameter	Min.	Typ.	Max.	Units	Conditions
$V_{(BR)CES}$	Collector-to-Emitter Breakdown Voltage	1200	—	—	V	$V_{GE} = 0V, I_C = 250\mu A$
$V_{(BR)ECS}$	Emitter-to-Collector Breakdown Voltage ④	18	—	—	V	$V_{GE} = 0V, I_C = 1.0 A$
$\Delta V_{(BR)CES}/\Delta T_J$	Temperature Coeff. of Breakdown Voltage	—	1.22	—	V/°C	$V_{GE} = 0V, I_C = 2.0 mA$
$V_{CE(ON)}$	Collector-to-Emitter Saturation Voltage	—	1.47	1.7	V	$I_C = 33A, V_{GE} = 15V$ See Fig.2, 5
		—	1.75	—		
		—	1.55	—		
$V_{GE(th)}$	Gate Threshold Voltage	3.0	—	6.0		$V_{CE} = V_{GE}, I_C = 250\mu A$
$DV_{GE(th)}/DT_J$	Temperature Coeff. of Threshold Voltage	—	-11	—	mV/°C	$V_{CE} = V_{GE}, I_C = 250\mu A$
$g_{fe}$	Forward Transconductance ⑤	27	40	—	S	$V_{CE} = 100V, I_C = 33A$
$I_{CES}$	Zero Gate Voltage Collector Current	—	—	250	$\mu A$	$V_{GE} = 0V, V_{CE} = 1200V$
		—	—	2.0		$V_{GE} = 0V, V_{CE} = 10V, T_J = 25^\circ C$
		—	—	1000		$V_{GE} = 0V, V_{CE} = 1200V, T_J = 150^\circ C$
$I_{GES}$	Gate-to-Emitter Leakage Current	—	—	$\pm 100$	nA	$V_{GE} = \pm 20V$

## Switching Characteristics @ $T_J = 25^\circ\text{C}$ (unless otherwise specified)

	Parameter	Min.	Typ.	Max.	Units	Conditions
$Q_g$	Total Gate Charge (turn-on)	—	167	251	nC	$I_C = 33A$ $V_{CC} = 400V$ See Fig. 8 $V_{GE} = 15V$
$Q_{ge}$	Gate - Emitter Charge (turn-on)	—	25	38		
$Q_{gc}$	Gate - Collector Charge (turn-on)	—	55	83		
$t_{d(on)}$	Turn-On Delay Time	—	32	—	ns	$T_J = 25^\circ C$ $I_C = 33A, V_{CC} = 960V$ $V_{GE} = 15V, R_G = 5.0\Omega$ Energy losses include "tail" See Fig. 9, 10, 14
$t_r$	Rise Time	—	29	—		
$t_{d(off)}$	Turn-Off Delay Time	—	845	1268		
$t_f$	Fall Time	—	425	638		
$E_{on}$	Turn-On Switching Loss	—	1.80	—	mJ	See Fig. 9, 10, 14
$E_{off}$	Turn-Off Switching Loss	—	19.6	—		
$E_{ts}$	Total Switching Loss	—	21.4	44		
$t_{d(on)}$	Turn-On Delay Time	—	32	—	ns	$T_J = 150^\circ C,$ $I_C = 33A, V_{CC} = 960V$ $V_{GE} = 15V, R_G = 5.0\Omega$ Energy losses include "tail" See Fig. 10,11,14
$t_r$	Rise Time	—	30	—		
$t_{d(off)}$	Turn-Off Delay Time	—	1170	—		
$t_f$	Fall Time	—	1000	—		
$E_{ts}$	Total Switching Loss	—	37	—	mJ	See Fig. 10,11,14
$L_E$	Internal Emitter Inductance	—	13	—	nH	Measured 5mm from package
$C_{ies}$	Input Capacitance	—	3600	—	pF	$V_{GE} = 0V$ $V_{CC} = 30V$ See Fig. 7 $f = 1.0MHz$
$C_{oes}$	Output Capacitance	—	160	—		
$C_{res}$	Reverse Transfer Capacitance	—	30	—		

### Notes:

- ① Repetitive rating;  $V_{GE} = 20V$ , pulse width limited by max. junction temperature. ( See fig. 13b )
- ②  $V_{CC} = 80\%(V_{CES}), V_{GE} = 20V, L = 10\mu H, R_G = 5.0\Omega,$  (See fig. 13a)
- ③ Repetitive rating; pulse width limited by maximum junction temperature.
- ④ Pulse width  $\leq 80\mu s$ ; duty factor  $\leq 0.1\%$ .
- ⑤ Pulse width  $5.0\mu s$ , single shot.

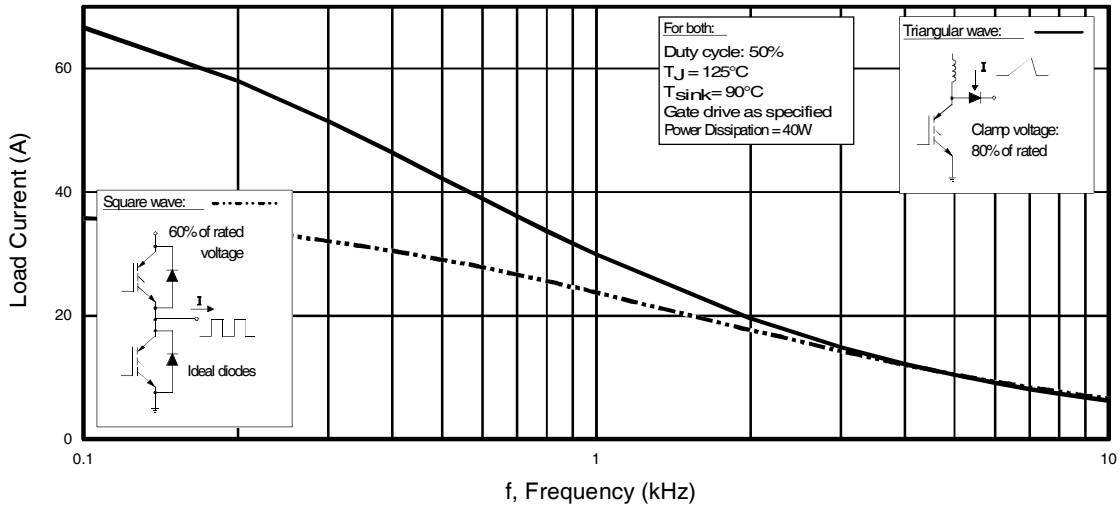


Fig. 1 - Typical Load Current vs. Frequency  
(Load Current =  $I_{\text{RMS}}$  of fundamental)

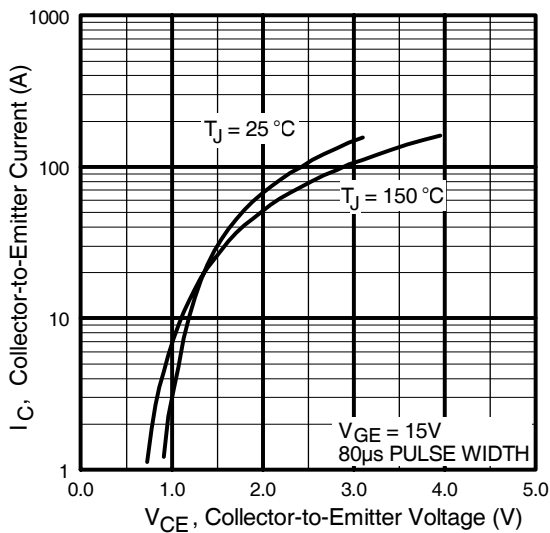


Fig. 2 - Typical Output Characteristics

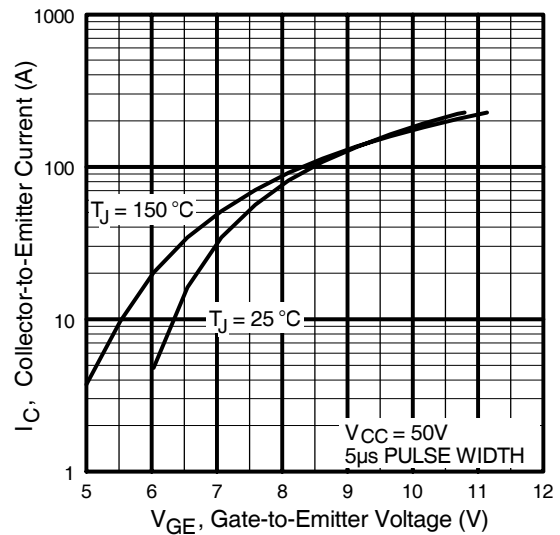
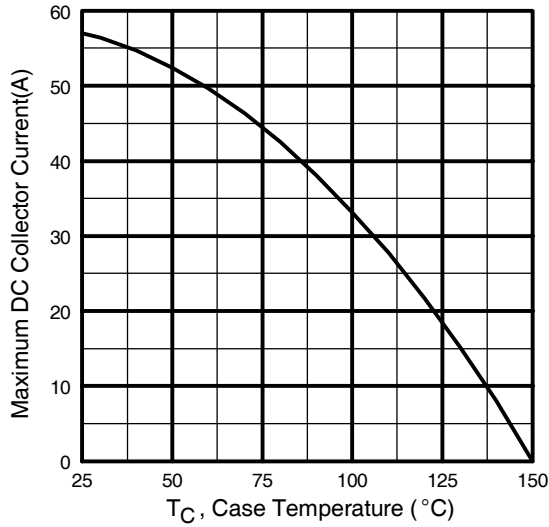


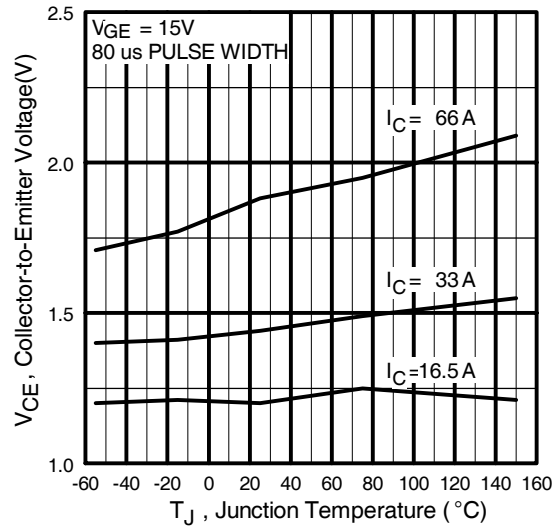
Fig. 3 - Typical Transfer Characteristics

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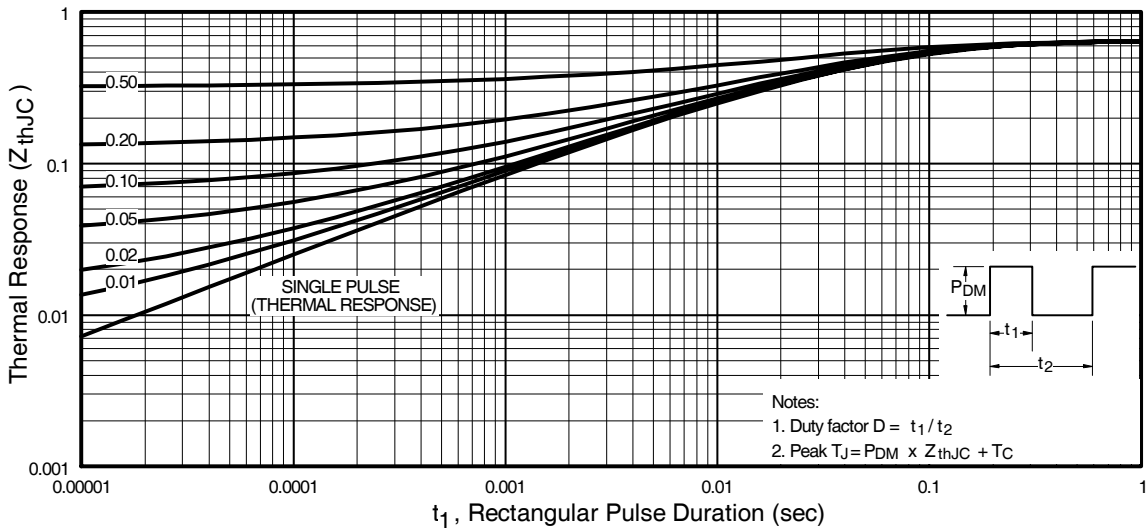
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**Fig. 4** - Maximum Collector Current vs. Case Temperature



**Fig. 5** - Typical Collector-to-Emitter Voltage vs. Junction Temperature



**Fig. 6** - Maximum Effective Transient Thermal Impedance, Junction-to-Case

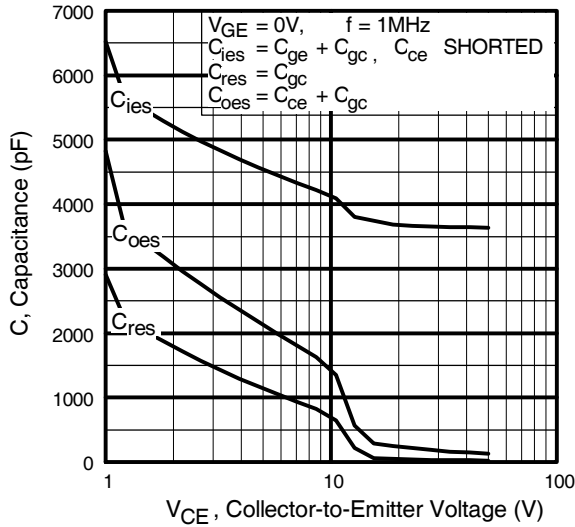


Fig. 7 - Typical Capacitance vs. Collector-to-Emitter Voltage

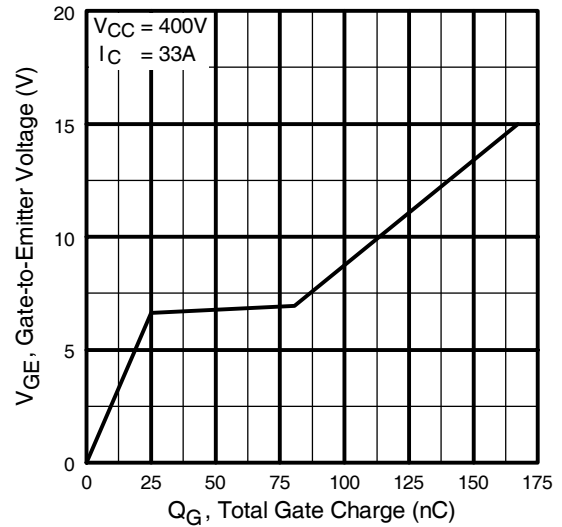


Fig. 8 - Typical Gate Charge vs. Gate-to-Emitter Voltage

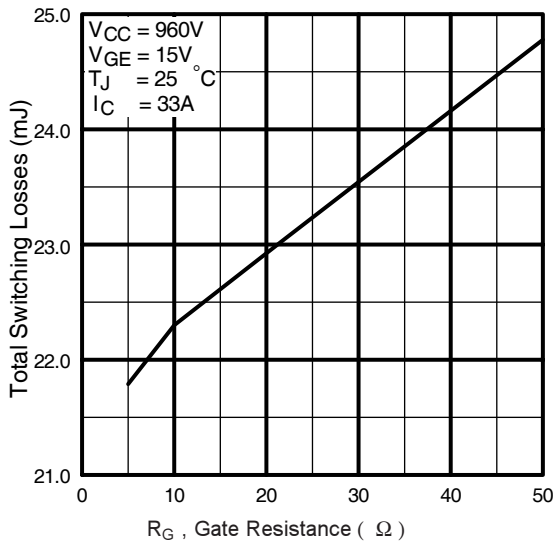


Fig. 9 - Typical Switching Losses vs. Gate Resistance

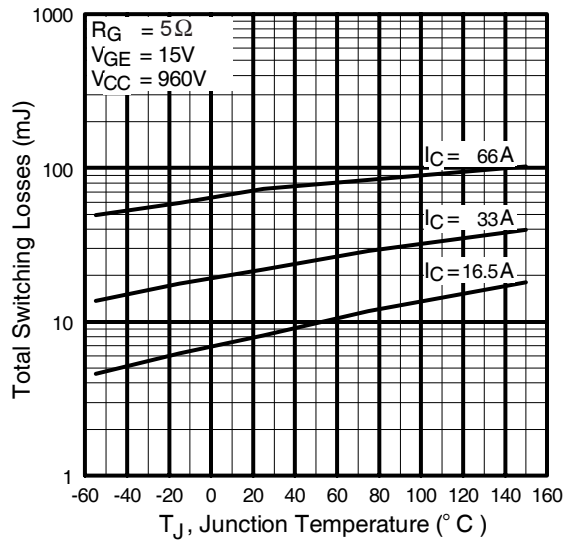
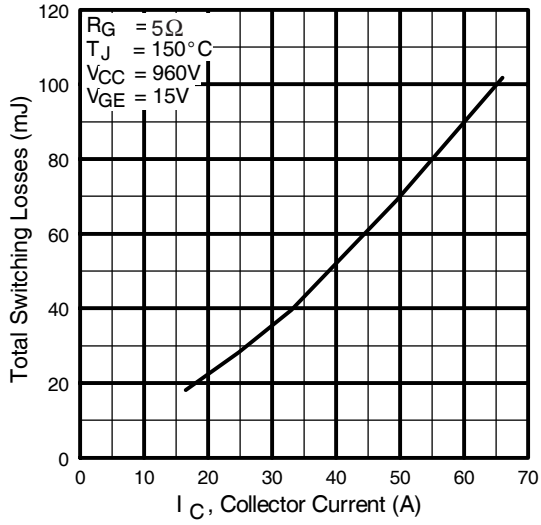


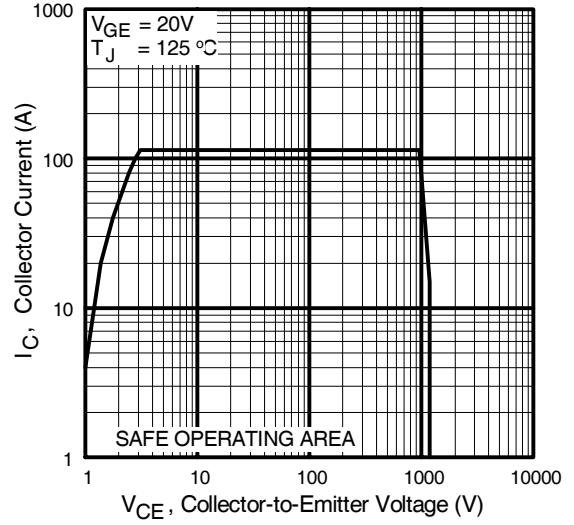
Fig. 10 - Typical Switching Losses vs. Junction Temperature

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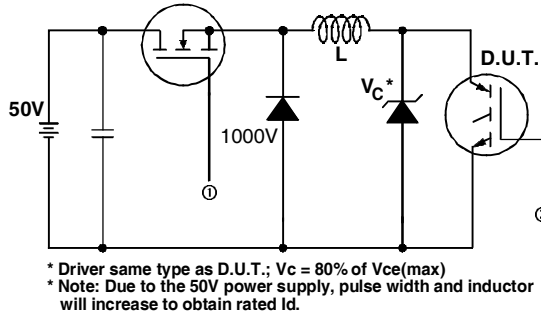
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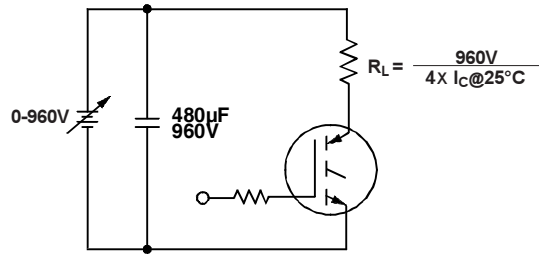
**Fig. 11** - Typical Switching Losses vs. Collector-to-Emitter Current



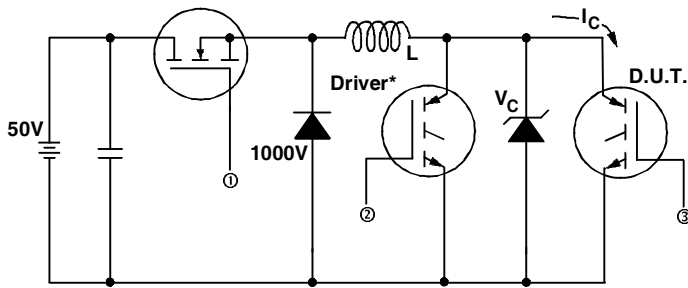
**Fig. 12** - Reverse Bias SOA



**Fig. 13a** - Clamped Inductive Load Test Circuit

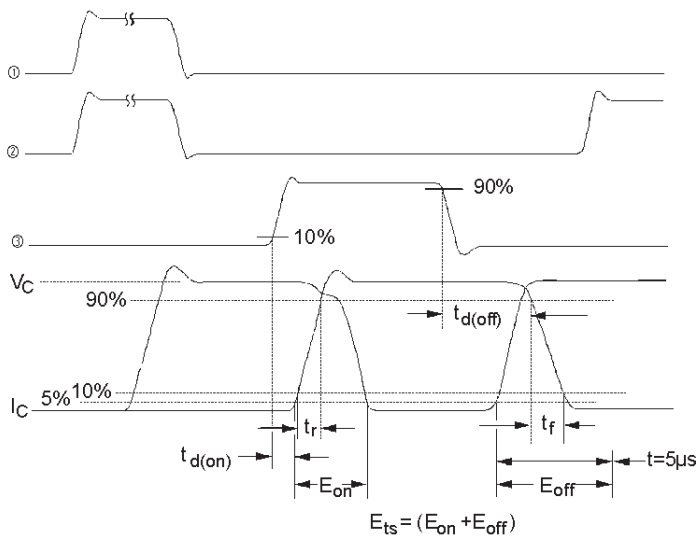


**Fig. 13b** - Pulsed Collector Current Test Circuit



**Fig. 14a** - Switching Loss Test Circuit

\* Driver same type as D.U.T., VC = ---V



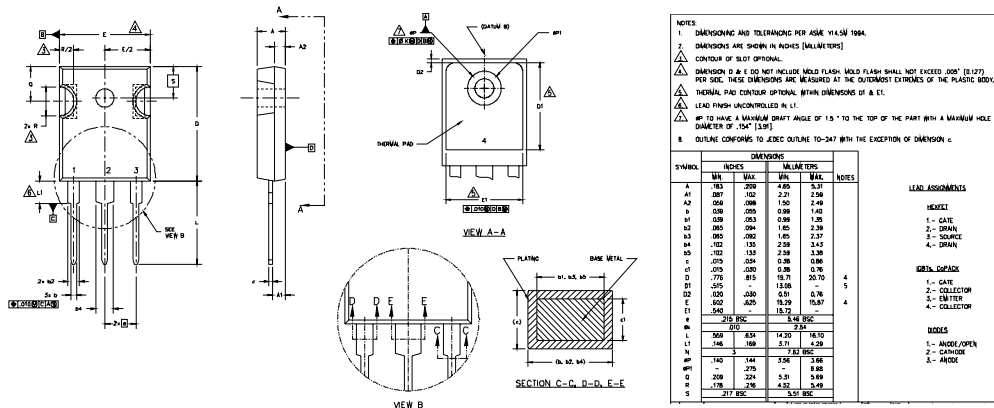
**Fig. 14b** - Switching Loss Waveforms

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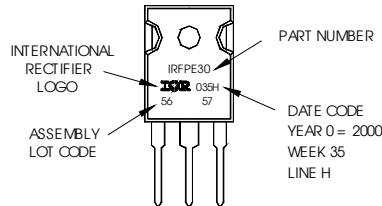
## TO-247AC Package Outline

Dimensions are shown in millimeters (inches)



## TO-247AC Part Marking Information

EXAMPLE: THIS IS AN IRFP30  
WITH ASSEMBLY  
LOT CODE 5657  
ASSEMBLED ON WW 35, 2000  
IN THE ASSEMBLY LINE "H"  
**Note:** "P" in assembly line  
position indicates "Lead-Free"



Data and specifications subject to change without notice.

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Note: For the most current drawings please refer to the IR website at:  
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